**Ted Johansson, LIST OF PUBLICATIONS**
updated 2024-06-21

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1. H. Norström, S. Nygren, T. Johansson, R. Buchta, M. Östling, A. Lindberg, U. Gustafsson, C. S. Petersson, "A Refined Polycide Gate Process With Silicided Diffusions for Submicron MOS Applications", J. Electrochem. Soc., 136, 805 (1989).
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25. P. K. B. Rangaiah, J. Engstrand, T. Johansson, M. D. Perez and R. Augustine, "92 Mb/s Fat-Intrabody Communication (Fat-IBC) With Low-Cost WLAN Hardware," in IEEE Transactions on Biomedical Engineering, vol. 71, no. 1, pp. 89-96, Jan. 2024. doi:10.1109/TBME.2023.3292405.

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